

17. (Twice Amended) The polishing pad used for polishing a semiconductor wafer according to Claim 14, wherein a content of zinc oxide (ZnO) in the porous surface layer is 100ppm or less at the ratio of zinc weight relative to the weight of the porous surface layer.

18. (Twice Amended) The polishing pad used for polishing a semiconductor wafer according to Claim 15, wherein a content of zinc oxide (ZnO) in the porous surface layer is 100ppm or less at the ratio of zinc weight relative to the weight of the porous surface layer.

20. (Twice Amended) A polishing pad used for polishing a semiconductor in a mirror polishing process, wherein it comprises a base layer formed of nonwoven fabric and a porous surface layer, and a content of zinc oxide (ZnO) included in the porous surface layer is 100ppm or less at the ratio of zinc weight relative to the weight of the porous surface layer.

21. (Twice Amended) The polishing pad for polishing a semiconductor wafer according to claim 20, wherein the porous surface layer does not include zinc oxide (ZnO).

27. (Twice Amended) A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 11.

28. (Twice Amended) A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 12.

29. (Twice Amended) A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 13.

30. (Amended) A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 20.